

IN THE SPECIFICATION:

Please replace paragraph [0008] with the following amended paragraph:

-- FIG. 3 is a cross sectional view along III-III of FIG. 2 according to the related art.

In FIG. 3, the OELD device has a driving thin film transistor (TFT) “ T_D ” and an organic electroluminescent (EL) diode “ D_{EL} .” The driving TFT “ T_D ” has a driving gate electrode 38, a driving active layer 42, a driving source electrode 56, and a driving drain electrode 52. In addition, a first electrode 16 is formed over the driving TFT “ T_D ” and is connected to the driving drain electrode 52 with an insulating layer 57 therebetween. The organic EL diode “ D_{EL} ” includes the first electrode 16, an organic electroluminescent (EL) layer 18, and a second electrode 20. The organic EL layer 18 is formed on the first electrode 16 for emitting light of a particular color wavelength, and the second electrode 20 is formed on the organic EL layer 18. A storage capacitor “ C_{ST} ” is connected in parallel to the driving TFT “ T_D ,” and includes first and second capacitor electrodes 15 and 35. The driving source electrode 56 contacts the second capacitor electrode 35, i.e., a power line, and the first capacitor electrode 15 is formed of polycrystalline silicon material under the second capacitor electrode 35. The second electrode 20 is formed on the substrate 12 upon which the driving TFT “ T_D ,” the storage capacitor “ C_{ST} ,” and the organic electroluminescent layer 18 are formed. Adjacent pixel regions may be divided by a sidewall.--